

FEATURES

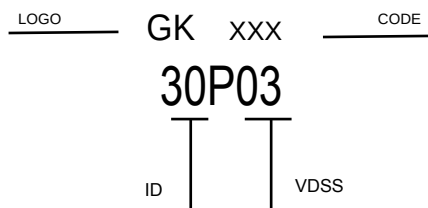
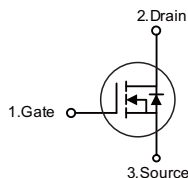
- -30V, -30A
 $R_{DS(ON)} < 17.4m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 23m\Omega @ V_{GS} = -4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

APPLICATION

- Load Switch
- PWM Application
- Power Management

100% UIS TESTED!
100% ΔV_{ds} TESTED!

V_{DSS} -30 V
 I_D -30 A
 $R_{DS(ON)}$ 17.4m Ω



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		-30	V
V_{GS}	Gate-to-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	-30	A
		$T_C = 100^\circ\text{C}$	15	
I_{DM}	Pulsed Drain Current ⁽¹⁾		-48	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾		7.8	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	30	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾		46	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.1	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	$^\circ\text{C}$

Electrical characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = -250μA, V _{GS} = 0V	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = -10V, I _D = -10A	-	13.4	17.4	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	17.7	23.0	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz	-	1267	-	pF
C _{oss}	Output Capacitance		-	166	-	pF
C _{rss}	Reverse Transfer Capacitance		-	126	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to -10V V _{DS} = -15V, I _D = -5A	-	23	-	nC
Q _{gs}	Gate Source Charge		-	4	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = -10V, V _{DD} = -15V I _D = -5A, R _{GEN} = 3Ω	-	4	-	ns
t _r	Turn-On Rise Time		-	3	-	ns
t _{d(off)}	Turn-Off DelayTime		-	60	-	ns
t _f	Turn-Off Fall Time		-	50	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-12	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-48	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -12A	-	-	-1.2	V
trr	Body Diode Reverse Recovery Time	I _F = -5A, di/dt = 100A/us	-	12	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	4	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. EAS condition: Starting $T_J=25^\circ\text{C}$, $V_{DD}=-15\text{V}$, $V_G=-10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=-8\text{A}$
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

RATING AND CHARACTERISTIC CURVES

Figure 1: Output Characteristics

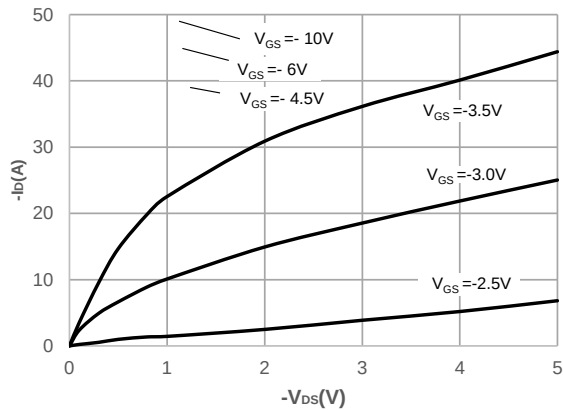


Figure 2: Typical Transfer Characteristics

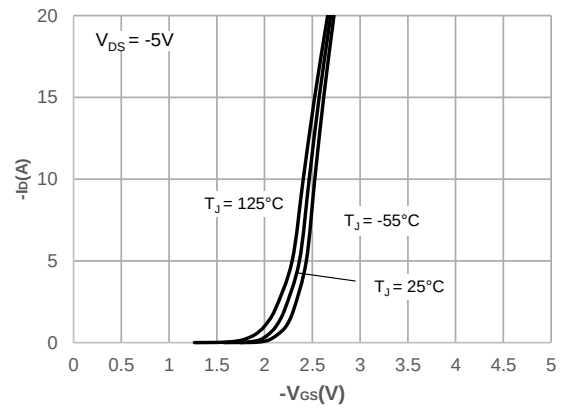


Figure 3: On-resistance vs. Drain Current

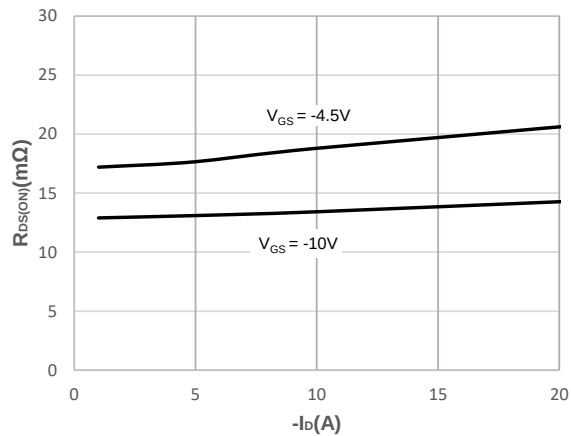


Figure 4: Body Diode Characteristics

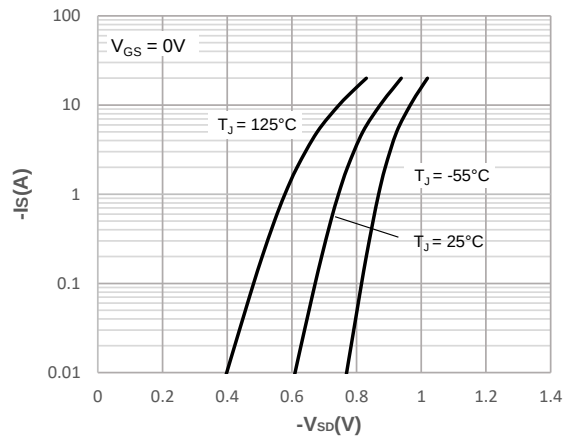


Figure 5: Gate Charge Characteristics

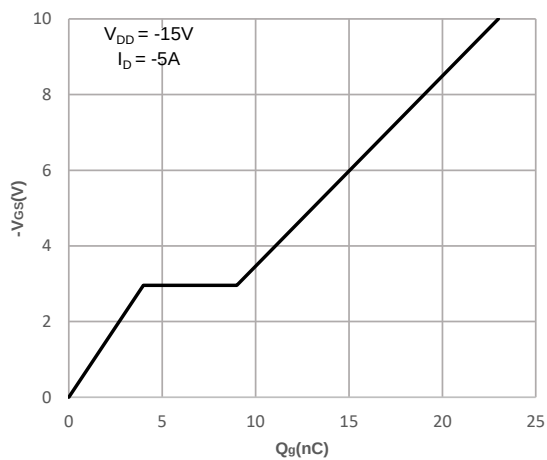
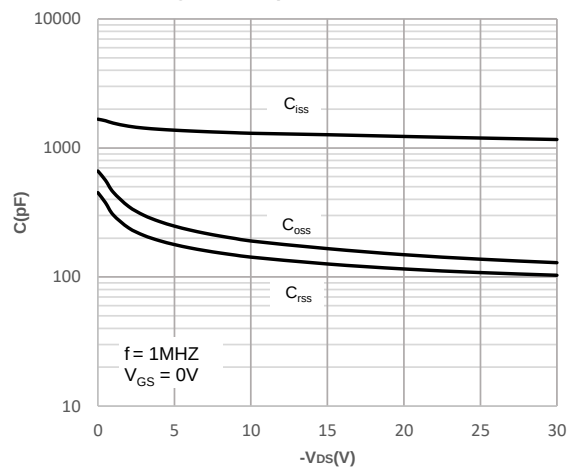


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

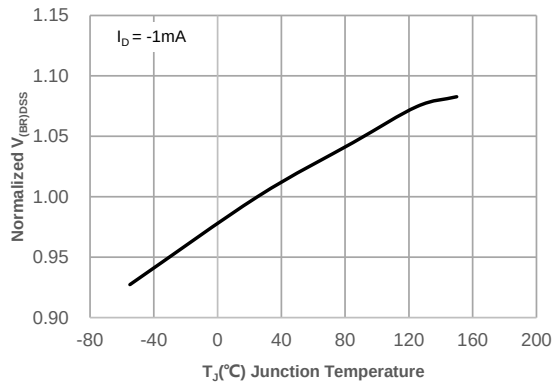


Figure 8: Normalized on Resistance vs. Junction Temperature

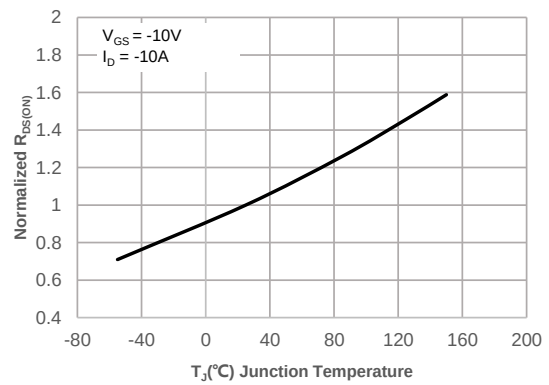


Figure 9: Maximum Safe Operating Area

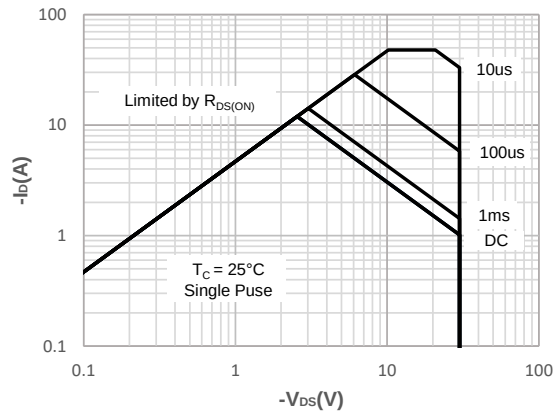


Figure 10: Maximum Continuous Driain Current vs. Case Temperature

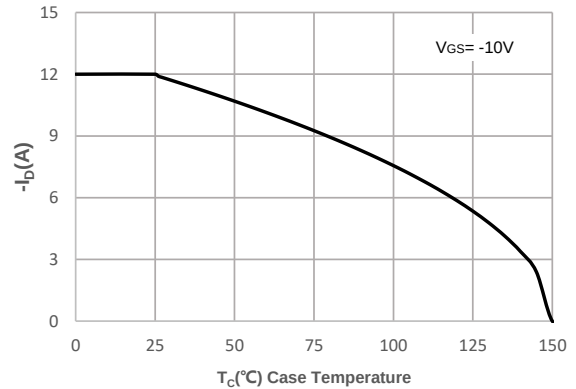


Figure 11: Normalized Maximum Transient Thermal Impedance

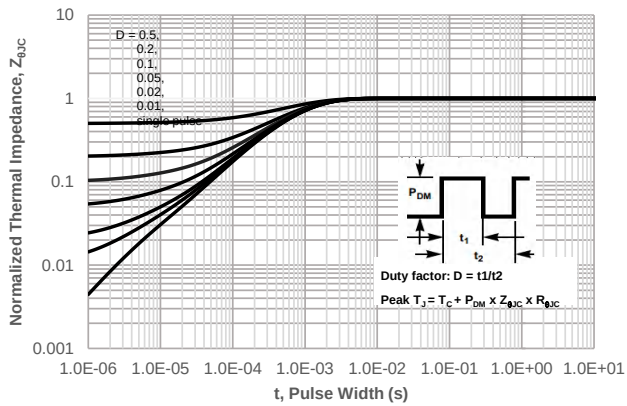
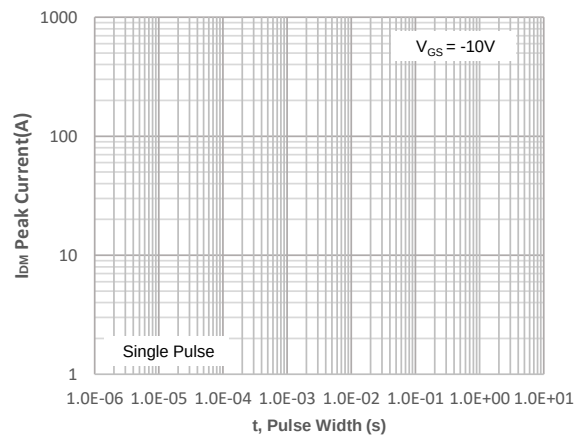


Figure 12: Peak Current Capacity



Test Circuit

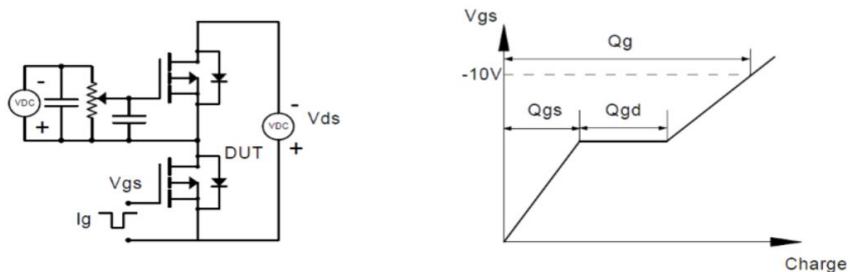


Figure 1: Gate Charge Test Circuit & Waveform

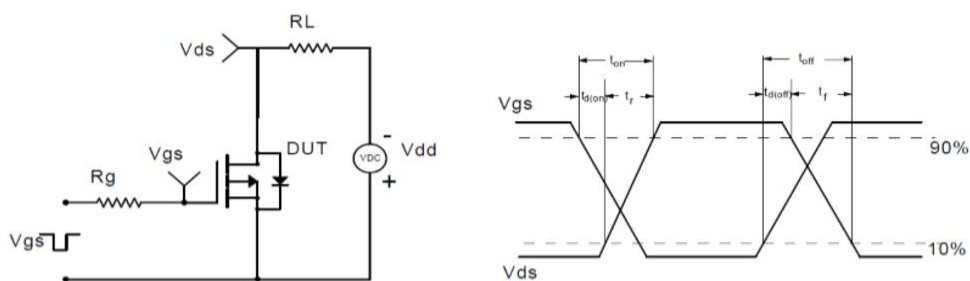


Figure 2: Resistive Switching Test Circuit & Waveform

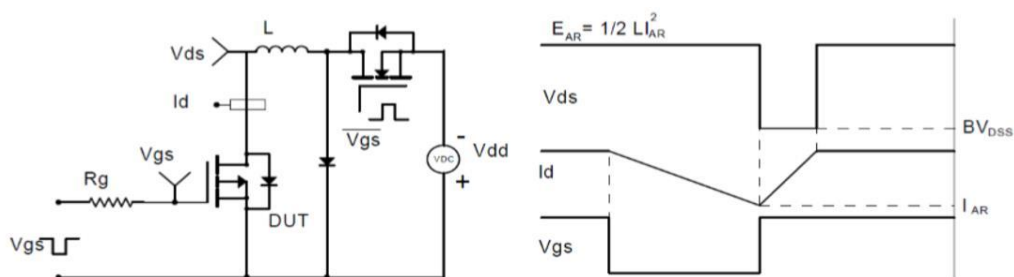


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

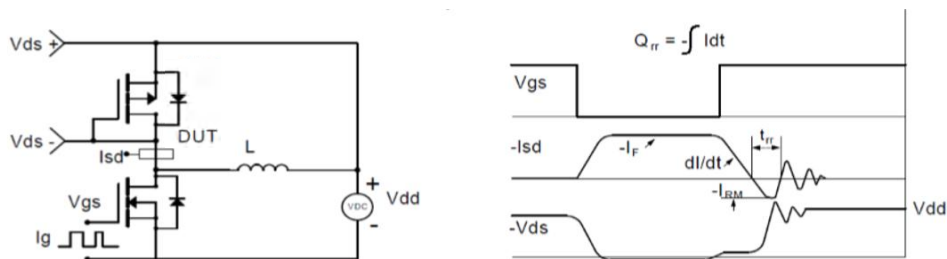
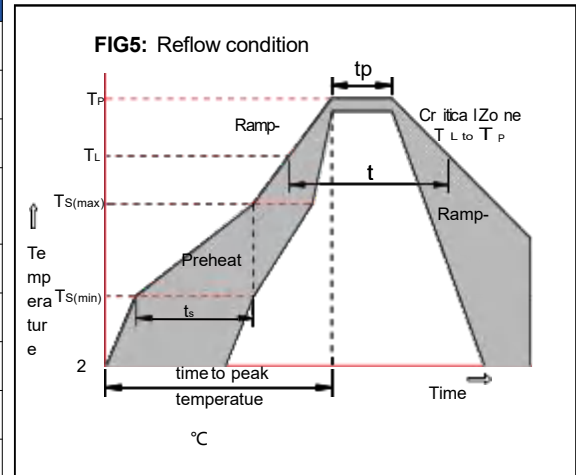


Figure 4: Diode Recovery Test Circuit & Waveform

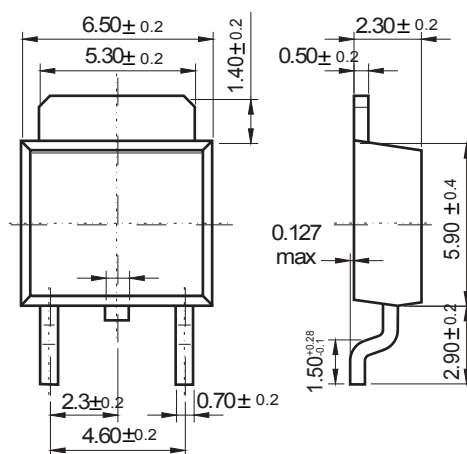
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

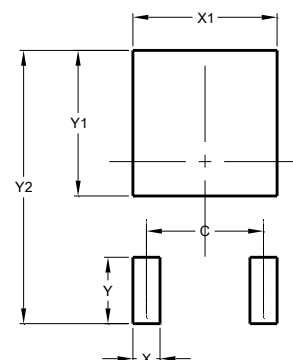


Package Dimensions & Suggested Pad Layout

TO-252



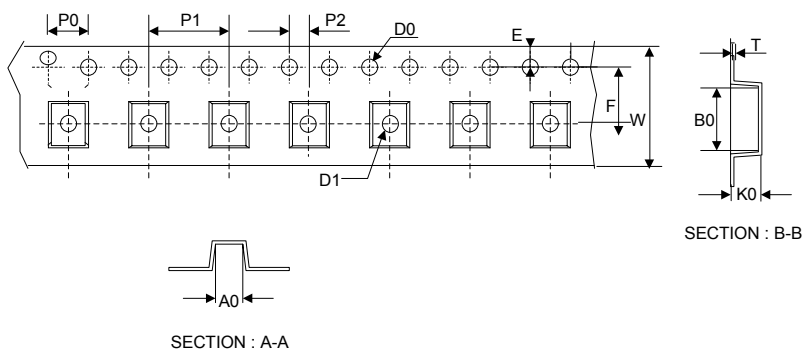
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

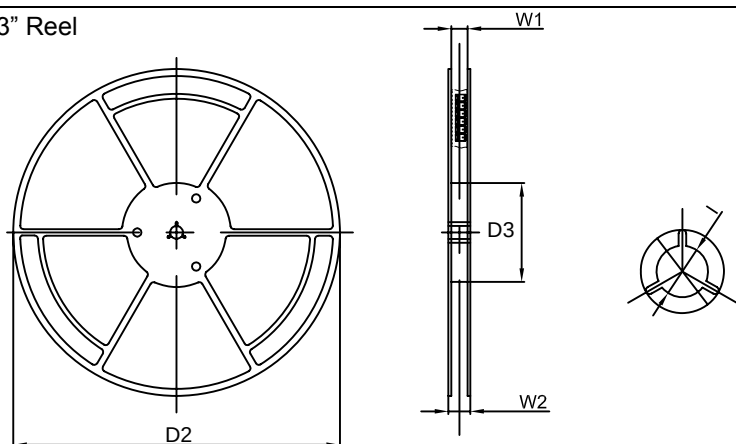
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.15
D1	1.55±0.20
E	1.75±0.20
F	7.50±0.20
W	16.00±0.20
A0	7.10±0.20
B0	10.50±0.20
K0	2.70±0.20
T	0.30±0.10
D2	330.0±5.0
D3	100.0±4.0
W1	20.0±5.0
W2	25.0±5.0
I	13.0±2.0

13" Reel



Quantity: 2500PCS